DMC50501

Silicon NPN epitaxial planar type

For general amplification
DMC20501 in SMini6 type package

■ Features

- \bullet High forward current transfer ratio h_{FE} with excellent linearity
- \bullet Low collector-emitter saturation voltage $V_{\text{CE}(\text{sat})}$
- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

■ Basic Part Number

Dual DSC2001 (Individual)

Packaging

DMC505010R Embossed type (Thermo-compression sealing): 3000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	60	V
Collector-emitter voltage (Base open)	V _{CEO}	50	V
Emitter-base voltage (Collector open)	V_{EBO}	7	V
Collector current	I_{C}	100	mA
Peak collector current	I_{CP}	200	mA
Total power dissipation	P _T	150	mW
Junction temperature	T_j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Package

• Code

SMini6-F3-B

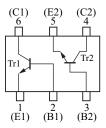
Package dimension clicks here.→

• Pin Name

1: Emitter (Tr1) 4: Collector (Tr2) 2: Base (Tr1) 5: Emitter (Tr2) 3: Base (Tr2) 6: Collector (Tr1)

■ Marking Symbol: B0

■ Internal Connection



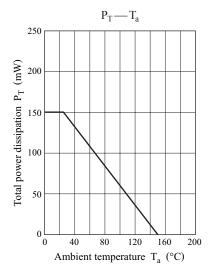
■ Electrical Characteristics $T_a = 25$ °C±3°C

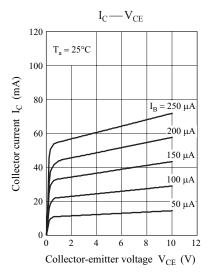
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_C = 10 \mu A, I_E = 0$	60			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = 2 \text{ mA}, I_{\rm B} = 0$	50			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 10 \mu A, I_C = 0$	7			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 20 \text{ V}, I_{E} = 0$			0.1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = 10 \text{ V}, I_{B} = 0$			100	μΑ
Forward current transfer ratio	h_{FE}	$V_{CE} = 10 \text{ V}, I_{C} = 2 \text{ mA}$	210		460	_
h _{FE} ratio *	h _{FE} (Small/Large)	$V_{CE} = 10 \text{ V}, I_{C} = 2 \text{ mA}$	0.50	0.99		_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$		0.13	0.3	V
Transition frequency	f_T	$V_{CE} = 10 \text{ V}, I_{C} = 2 \text{ mA}$		150		MHz
Collector output capacitance (Common base, input open circuited)	C _{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		1.5		pF

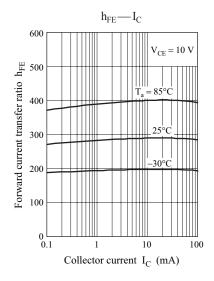
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

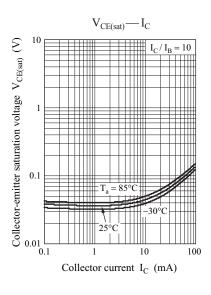
^{2. *:} Ratio between 2 elements

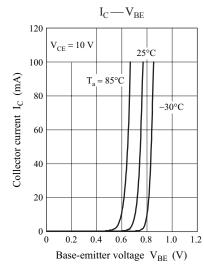
DMC50501 Panasonic

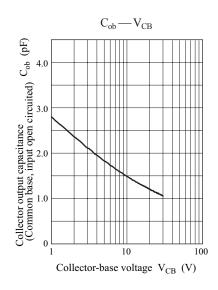


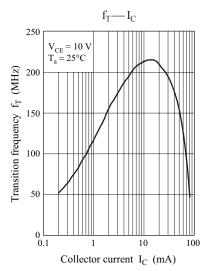












2 Ver. BED

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